

FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. DLED.004CP1C1	APPLICATION NO. 10/689,544
INFORMATION DISCLOSURE STATEMENT BY APPLICANT			
(USE SEVERAL SHEETS IF NECESSARY)			
		FILING DATE October 20, 2003	GROUP 2842 2826

U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
MLT	1	4,063,189	12/13/77	Scifres et al.	—	—	—
	2	5,101,413	3/31/92	Botez			
	3	5,537,433	7/16/96	Watanabe			
	4	5,705,834	1/1998	Egalon et al.			
	5	5,779,924	7/1998	Krames et al.			
	6	5,793,062	8/1998	Kish, Jr. et al.			
	7	5,818,860	10/1998	Garbuzov			
	8	6,057,562	5/2000	Lee et al.			
	9	6,429,462	8/2002	Shveykin			
MLT	10	6,649,938	11/2003	Bogatov et al.	—	—	—

FOREIGN PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
							YES NO
MLT	11	SU 1329533 A1	05/1998	Soviet Union			X
	12	SU 1359833 A1	15/12/87	Soviet Union			X
	13	1,455,373	30/01/89	Soviet Union			
	14	2,133,534	7/20/99	Russia			
	15	2,134,007	07/27/99	Russia			X
	16	2,142,661	12/10/99	Russia			X
	17	2,142,665	12/10/99	Russia			X
	18	EP 0 247 267 B1	10/1991	Europe			
	19	EP 0727827 A3	21/08/96	Europe			
	20	EP 0849812 A3	24/06/98	Europe			
	21	60-211993	10/1985	Japan			
	22	WO 85/03809 A1	29/08/85	WIPO			
	23	WO 99/46838	09/1999	WIPO			X
MLT	24	WO 99/08352	02/1999	WIPO			

EXAMINER Minhloan Tran	DATE CONSIDERED	6/05
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FOREIGN PATENT DOCUMENTS							
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							YES NO
MLT	25	WO 00/10235	02/2000	WIPO			X
MLT	26	WO 00/39860	07/2000	WIPO			X

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)						
MLT	27	<i>High-Efficiency InGaAlP Visible Light-Emitting Diodes</i> , H. Sugawara et al., <i>Japanese Journal of Applied Physics</i> , Vol. 31, No. 8, August 1992, pp. 2446-2451.					
	28	<i>Room-Temperature CW Operation of InGaAsP Lasers on Si Fabricated by Wafer Bonding</i> , H. Wada et al., <i>IEEE Photonics Technology Letters</i> , Vol. 8, No. 2, February 1996, pp. 173-175.					
	29	<i>Chemically Assisted Ion Beam Etching of GaAs, Ti, and Mo</i> , J. D. Chinn et al., <i>J. Vac. Sci. Technol. A</i> , Vol. 1, No. 2, April-June 1983, pp. 701-704.					
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	31	<i>Thin-Films Field-Transfer Matrix Theory of Planar Multilayer Waveguides and Reflection From Prism-Loaded Waveguides</i> , J. Chilwell et al., <i>Journal of the Optical Society of America</i> , Vol. 1, No. 7, July 1984, pp. 742-753.					
	32	<i>Wide Spectrum Single Quantum Well Superluminescent Diodes At 0.8μm With Bent Optical Waveguide</i> , A. T. Semenov et al., <i>Electronics Letters</i> , Vol. 29, No. 10, May 13, 1993, pp. 854-855.					
	33	<i>Superluminescent Diodes with Bent Waveguide</i> , C.-F. Lin et al., <i>IEEE Photonics Technology Letters</i> , Vol. 8, No. 2, February 1996, pp. 206-208.					
	34	<i>Low spectral modulation high-power output from a new AlGaAs superluminescent diode/optical amplifier structure</i> , G. A. Alphonse et al., <i>Applied Physics Letters</i> , Vol. 55, No. 22, November 27, 1989, pp. 2289-2291.					
	35	<i>P-GaN/N-InGaN/N-GaN Double Heterostructure Blue-Light-Emitting Diodes</i> , S. Nakamura et al., <i>Japanese Journal of Applied Physics</i> , Vol. 32, Part 2, No. 1A/B, January 15, 1993, pp. L8-L11.					
	36	<i>High-Brightness AlGaN/P 573-nm Light-Emitting Diode with A Chirped Multiquantum Barrier</i> , C. S. Chang et al., <i>IEEE Journal of Quantum Electronics</i> , Vol. 34, No. 1, January 1998, pp. 77-83.					
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	38	<i>Superbright Green InGaN Single-Quantum-Well-Structure Light-Emitting Diodes</i> , S. Nakamura et al., <i>Japanese Journal of Applied Physics</i> , Vol. 34 (1995) pp. L1332-L1335, Part 2, No. 10B, 15 October 1995.					
	39	<i>Internal Optical Losses in Very Thin CW Heterojunction Laser Diodes</i> , J. K. Butler et al., <i>IEEE Journal of Quantum Electronics</i> , Vol. QE-11, No. 7, July 1975 pp. 402-408.					
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	41	<i>Optoelektronika [Optoelectronics]</i> , Yu. R. Nosov, <i>Radio i svyaz</i> , [Radio and Communications], Moscow, Publ. (1989), pp. 136-143.					
	42	<i>Light-Emitting Diodes with 17% External Quantum Efficiency at 622 Mb/s for High-Bandwidth Parallel Short-Distance Optical Interconnects</i> , R. H. Windisch et al., <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , Vol. 5, No. 2, March/April 1999, pp. 166-171.					
	43	<i>High Brightness Visible (660 nm) Resonant-Cavity Light-Emitting Diode</i> , K. Streubel et al., <i>IEEE Photonics Technology Letters</i> , Vol. 10, No. 12, December 1998, pp. 1685-1687.					
MLT	44	<i>100-mW High-Power Angled-Stripe Superluminescent Diodes with a New Real Refractive-Index-Guided Self-Aligned Structure</i> , T. Takayama et al., <i>IEEE Journal of Quantum Electronics</i> , Vol. 32, No. 11, November 1996, pp. 1981-1987.					

EXAMINER	Minhloan Tran	DATE CONSIDERED	6/05
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EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)		
MLT	45	<i>High-power, high-efficiency 1.3 μm superluminescent diodes with a buried bent absorbing guide structure</i> , Haruo Nagai et al., <i>Applied Physics Letters</i> , Volume 54, Number 18, May 1989, pp. 1719-1721.	
	46	<i>High power, high efficiency window buried heterostructure GaAlAs superluminescent diode with an integrated absorber</i> , N. S. K. Kwong et al., <i>Applied Physics Letters</i> , Vol. 51, No. 23, December 7, 1987, pp. 1879-1881.	
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	48	<i>Measurement of the Modal Reflectivity of an Antireflection Coating on a Superluminescent Diode</i> , I. P. Kaminow et al., <i>IEEE Journal of Quantum Electronics</i> , Vol. QE-19, No. 4, April 1983, pp. 493-495.	
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	50	<i>High-Power Near-Diffraction-Limited Tapered Amplifiers at 1064 nm for Optical Intersatellite Communications</i> , P. Chazan et al., <i>IEEE Photonics Technology Letters</i> , Vol. 10, No. 11, November 1998, pp. 1542-1544.	
	51	<i>Extremely Low Power Consumption Semiconductor Optical Amplifier Gate for WDM Applications</i> , T. Ito et al., <i>Electronics Letters</i> , Vol. 33, No. 21, October 9, 1997, pp. 1791-1792.	
	52	<i>5-W CW Diffraction-Limited InGaAs Broad-Area Flared Amplifier at 970 nm</i> , S. O'Brien et al., <i>IEEE Photonics Technology Letters</i> , Vol. 9, No. 9, September 1997, pp. 1217-1219.	
	53	<i>Wavelength Conversion Using Semiconductor Optical Amplifiers</i> , M. Asghari et al., <i>Journal of Lightwave Technology</i> , Vol. 15, No. 7, July 1997, pp. 1181-1190.	
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	56	<i>Progress in Long-Wavelength Strained-Layer InGaAs(P) Quantum-Well Semiconductor Laser and Amplifiers</i> , P. J. A. Thijss et al., <i>IEEE Journal of Quantum Electronics</i> , Vol. 30, No. 2, February 1994, pp. 477-499.	
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	58	<i>High-Power Diffraction-Limited Monolithic Broad Area Master Oscillator Power Amplifier</i> , S. O'Brien et al., <i>IEEE Photonics Technology Letters</i> , Vol. 5, No. 5, May 1993, pp. 526-528.	
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	60	<i>2.0 W CW, Diffraction-Limited Tapered Amplifier with Diode Injection</i> , D. Mehuys et al., <i>Electronics Letters</i> , Vol. 28, No. 21, October 8, 1992, pp. 1944-1946.	
	61	<i>Semiconductor Optical Amplifiers</i> , N. Anders Olsson, <i>Proceedings of IEEE</i> , Vol. 80, No. 3, March 1992, pp. 375-382.	
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	63	<i>546 km, 140 Mbit/s FSK Coherent Transmission Experiment through 10 Cascaded Semiconductor Laser Amplifiers</i> , S. Ryu et al., <i>Electronics Letters</i> , Vol. 25, No. 25, December 7, 1989, pp. 1682-1684.	
	64	<i>Pulse Energy Gain Saturation in Subpicosecond and Picosecond Pulse Amplification by a Traveling-Wave Semiconductor Laser Amplifier</i> , T. Saitoh et al., <i>IEEE Photonics Technology Letters</i> , Vol. 1, No. 10, October 1989, pp. 297-299.	
	65	<i>Polarization-Independent Optical Amplifier with Buried Facets</i> , N. A. Olsson et al., <i>Electronics Letters</i> , Vol. 25, No. 16, August 3, 1989, pp. 1048-1049.	
	66	<i>Gain and Noise Characteristics of a 1.5μm Near-travelling-wave Semiconductor Laser Amplifier</i> , J.-C. Simon et al., <i>Electronics Letters</i> , Vol. 25, No. 7, March 30, 1989, pp. 434-436.	
MLT	67	<i>1.3μm Semiconductor Laser Power Amplifier</i> , N. A. Olsson et al., <i>IEEE Photonics Technology Letters</i> , Vol. 1, No. 1, January 1989, pp. 2-3.	

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MLT	68	<i>Semiconductor Laser Optical Amplifiers for Use in Future Fiber Systems</i> , M. J. O'Mahony, <u>Journal of Lightwave Technology</u> , Vol. 6, No. 4, April 1988, pp. 531-544.	
	69	<i>New Inline Wideband Dynamic Semiconductor Laser Amplifier Model</i> , A. J. Lowery, <u>IEEE Proceedings</u> , Vol. 135, Pt J, No. 3, June 1988, pp. 242-250.	
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	71	<i>Fabrication and Performance of 1.5μm GaInAsP Travelling wave Laser Amplifiers with Angled Facets</i> , C. E. Zah et al., <u>Electronics Letters</u> , Vol. 23, No. 19, September 10, 1987, pp. 990-991.	
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	77	<i>High-power and high temperature long-term stability of Al-free 950nm laser structures on GaAs</i> , G. Beister et al., <u>Electronics Letters</u> , Vol. 35, No. 19, September 16, 1999, pp. 1641-1643.	
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	81	<i>High-Power High-Efficiency 0.98-μm Wavelength InGaAs-(In)GaAs(P)-InGaP Broadened Waveguide Lasers Grown by Gas-Source Molecular Beam Epitaxy</i> , M. R. Gokhale et al., <u>IEEE Journal of Quantum Electronics</u> , Vol. 33, No. 12, December 1997, pp. 2266-2276.	
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	83	<i>66% CW wallplug efficiency from Al-free 0.98μm-emitting diode lasers</i> , D. Botez et al., <u>Electronics Letters</u> , Vol. 32, No. 21, October 10, 1996, pp. 2012-2013.	
	84	<i>A Novel Cladding Structure for Semiconductor Quantum-Well Lasers with Small Beam Divergence and Low Threshold Current</i> , S. Yen et al., <u>IEEE Journal of Quantum Electronics</u> , Vol. 32, No. 9, September 1996, pp. 1588-1595.	
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	86	<i>Aluminum-Free 980-nm GaInAs/GaInAsP/GaInP Pump Lasers</i> , Harry Asonen et al., <u>IEEE Journal of Quantum Electronics</u> , Vol. 30, No. 2, February 1994, pp. 415-423.	
	87	<i>600 mW CW Single-Mode GaAlAs Triple-Quantum-Well Laser with a New Index Guided Structure</i> , O. Imafuji et al., <u>IEEE Journal of Quantum Electronics</u> , Vol. 29, No. 6, June 1993, pp. 1889-1894.	
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MLT	90	<i>High-Power 1.3-μm InGaAsP-InP Amplifiers with Tapered Gain Regions</i> , J.P. Donnelly et al., <u>IEEE Photonics Technology Letters</u> , Vol. 8, No. 11, November 1996, pp. 1450-1452.	

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MLT	91	<i>High-Power, Near-Diffraction-Limited Large-Area Traveling-Wave Semiconductor Amplifier</i> , L. Goldberg et al., <u>IEEE Journal of Quantum Electronics</u> , Vol. 29, No. 6, June 1993, pp. 2028-2043.	
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	93	<i>Monolithic Super-Bright Red Resonant Cavity Light-Emitting Diode Grown by Solid Source Molecular Beam Epitaxy</i> , M. Jalonens et al., <u>IEEE Photonics Technology Letters</u> , Vol. 10, No. 7, July 1998, pp. 923-925.	
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	99	<i>Nature of Wavelength Chirping in Directly Modulated Semiconductor Lasers</i> , T. L. Koch et. al., <u>Electronics Letters</u> , December 6, 1984, Vol. 20, No. 25/26, pp. 1038-1039.	
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	107	<i>Directional radiation pattern of quantum-dimensional InGaAs/GaAs leaky-mode lasers</i> , V.I. Shveikin et al., <u>Quantum Electronics</u> , Vol. 26, No. 1, 1999, pp. 33-36. (In Russian)	
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	110	Abstract of Russian Patent #RU 2133534 obtained from Delphion database (www.delphion.com).	
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	112	<i>GaN microdisk light emitting diodes</i> , S. X. Jin et al., <u>Applied Physics Letters</u> , Vol. 76, No. 5, January 31, 2000, pp. 631-633	
	113	<i>Improved characteristics of InGaN multiple-quantum-well light-emitting diode by GaN/Al/GaN distributed Bragg reflector grown on sapphire</i> , N. Nakada et al., <u>Applied Physics Letters</u> , Vol. 76, No. 14, April 3, 2000, pp. 1804-1806	
MLT	114	<i>Room-temperature operation at 333 nm of $\text{Al}_{0.03}\text{Ga}_{0.97}\text{N}/\text{Al}_{0.25}\text{Ga}_{0.75}\text{N}$ quantum-well light-emitting diodes with Mg-doped superlattice layers</i> , A. Kinoshita et al., <u>Applied Physics Letters</u> , Vol. 77, No. 2, July 10, 2000, pp 175-177	

EXAMINER	Minhloan Tran	DATE CONSIDERED	6/05
*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 608; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.			

FORM PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. DLED.004CP1C1	APPLICATION NO. 10/689,544
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		APPLICANT Vasily I. Shveykin	
(USE SEVERAL SHEETS IF NECESSARY)		FILING DATE October 20, 2003	GROUP 2812

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)		
MLT	115	<i>Resonant-cavity InGaN quantum-well blue light-emitting diodes</i> , Y.-K. song et al., <u>Applied Physics Letters</u> , Vol. 77, No. 12, September 18, 2000, pp 1744-1746	
MLT	116	<i>Green electroluminescent (Ga, In, Al) N LEDs grown on Si (111)</i> , S. Dalmasso et al., <u>Electronics Letters</u> , Vol. 36, No. 20, September 28, 2000, pp 1728-1730	
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MLT	118	<i>Semiconductor Optical Amplifiers</i> , J.-R. Kim et al., <u>Compound Semiconductor</u> , Vol. 6, No. 2, March 2000, pp. 46-48, 50	

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